

Silicon NPN Power Transistors

2SD2580

DESCRIPTION

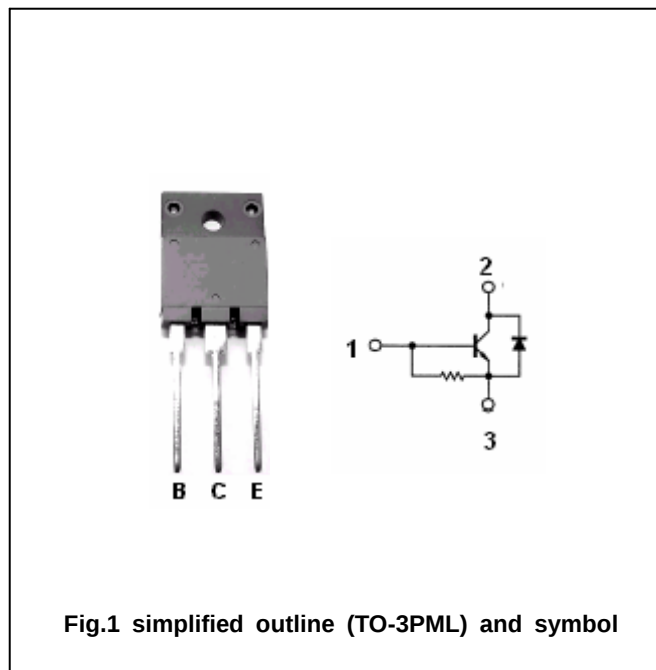
- With TO-3PML package
- High speed
- High breakdown voltage
- High reliability
- Built-in damper diode

APPLICATIONS

- Color TV horizontal deflection output

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		10	A
I_{CM}	Collector current-peak		30	A
P_C	Collector power dissipation	$T_C=25$	70	W
			3	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =100mA; I _B =0	800			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =8 A; I _B =1.6A			5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =8 A; I _B =1.6A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =800V; I _E =0			10	μ A
I _{CES}	Collector cut-off current	V _{CE} =1500V ; R _{BE} =0			1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =4V; I _C =0	40		130	mA
h _{FE-1}	DC current gain	I _C =8A ; V _{CE} =5V	5		8	
h _{FE-2}	DC current gain	I _C =1A ; V _{CE} =5V	15		30	
t _f	Fall time	I _C =6A; R _L =33.3 Ω I _{B1} =1.2A; -I _{B2} =2.4A; V _{CC} =200V			0.3	μ s

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PACKAGE OUTLINE

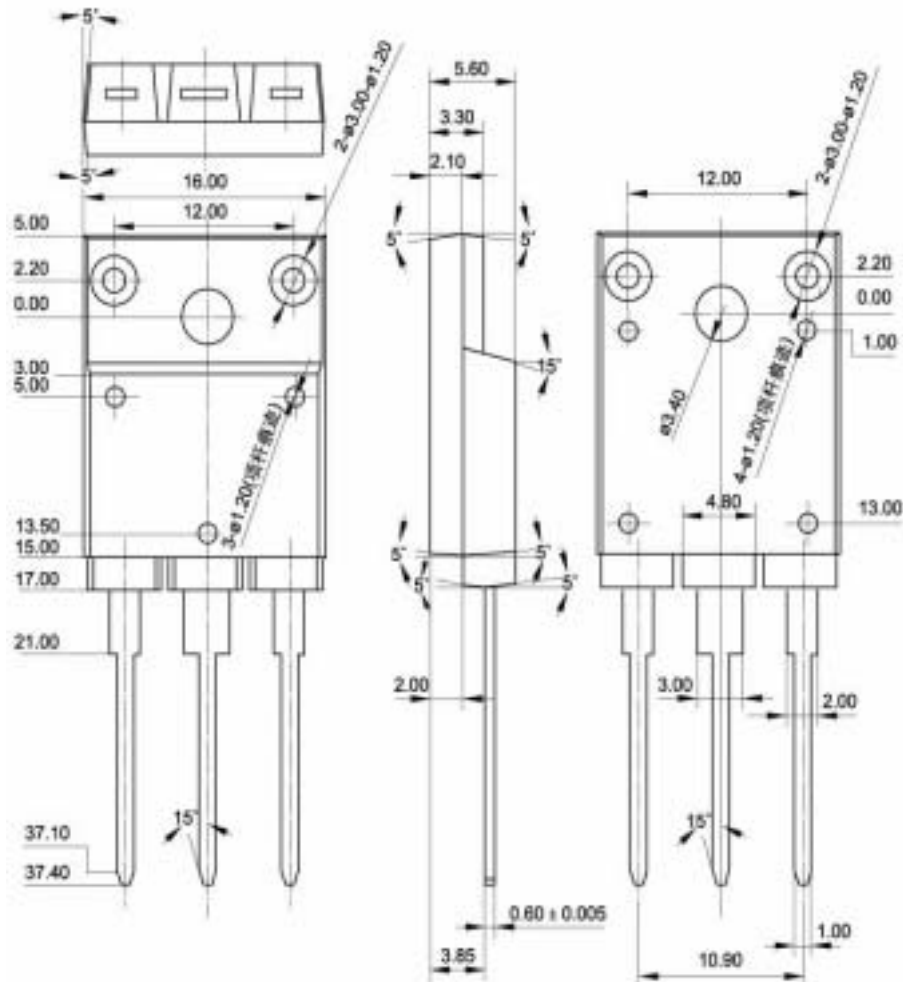


Fig.2 Outline dimensions

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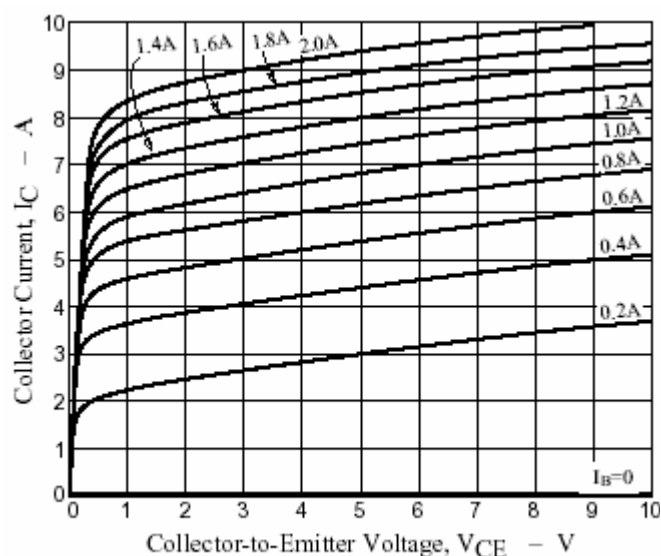


Fig.3 Static Characteristic

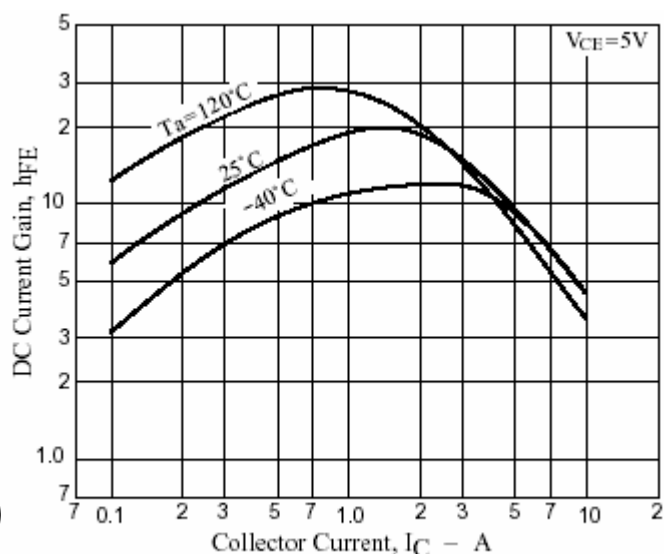


Fig.4 DC current Gain

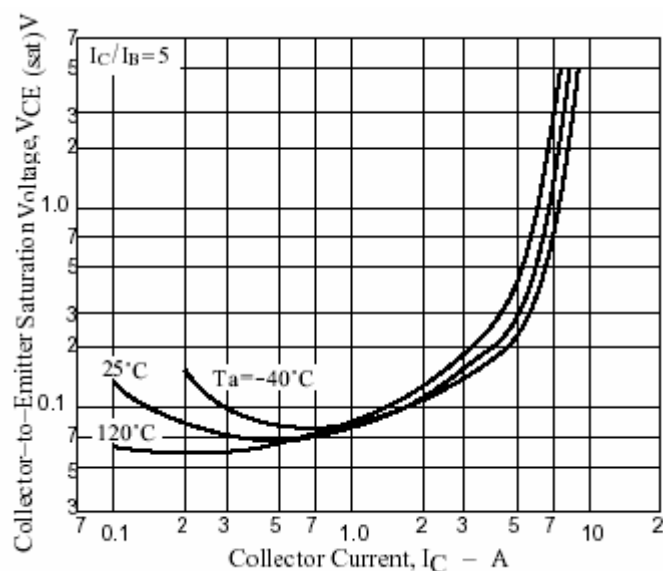


Fig.5 Collector-Emitter Saturation Voltage

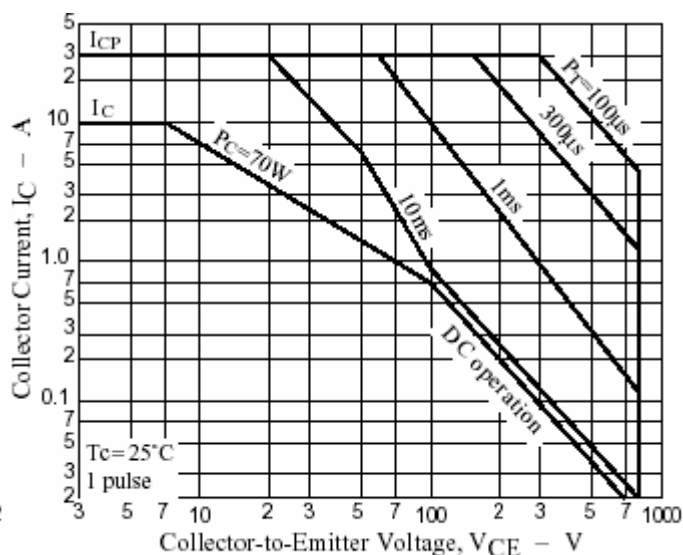


Fig.6 Safe Operating Area